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Team Nexperia

## PEMB11; PUMB11

# PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

Rev. 3 — 30 November 2011

Product data sheet

### 1. Product profile

#### 1.1 General description

PNP/PNP Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	number Package		NPN/PNP	NPN/NPN	Package
	NXP	JEITA	complement	complement	configuration
PEMB11	SOT666	-	PEMD3	PEMH11	ultra small and flat lead
PUMB11	SOT363	SC-88	PUMD3	PUMH11	very small

#### 1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

#### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		0.8	1.0	1.2	



PNP/PNP resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

### 2. Pinning information

Table 3. Pinning

riiiiiig		
Description	Simplified outline	Graphic symbol
GND (emitter) TR1		
input (base) TR1	6   5   4	6 5 4
output (collector) TR2		
GND (emitter) TR2		R1 R2
input (base) TR2	البــــــــــــــــــــــــــــــــــــ	TR1
output (collector) TR1	001aab555	R2 R1 1 2 3 006aaa212
	Description GND (emitter) TR1 input (base) TR1 output (collector) TR2 GND (emitter) TR2 input (base) TR2	Description  GND (emitter) TR1 input (base) TR1 output (collector) TR2 GND (emitter) TR2 input (base) TR2

### 3. Ordering information

Table 4. Ordering information

Type number	Package	Package		
	Name	Description	Version	
PEMB11	<b>'-</b>	plastic surface-mounted package; 6 leads	SOT666	
PUMB11	SC-88	plastic surface-mounted package; 6 leads	SOT363	

### 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMB11	B1
PUMB11	B*1

[1] \* = placeholder for manufacturing site code.

### 5. Limiting values

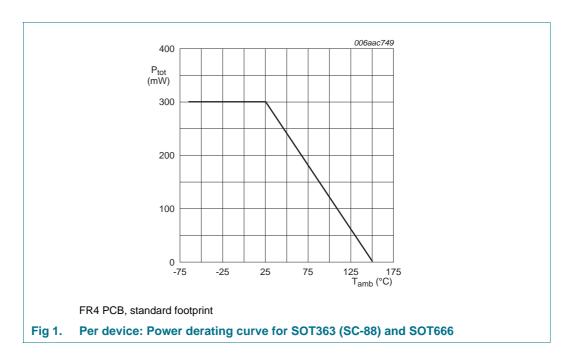
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
$V_{CBO}$	collector-base voltage	open emitter	-	-50	V
$V_{CEO}$	collector-emitter voltage	open base	-	-50	V
$V_{EBO}$	emitter-base voltage	open collector	-	-10	V
$V_{I}$	input voltage				
	positive		-	+10	V
	negative		-	-40	V
Io	output current		-	-100	mA
I <sub>CM</sub>	peak collector current		-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u>		
	PEMB11 (SOT666)		[2] _	200	mW
	PUMB11 (SOT363)		-	200	mW
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u>		
	PEMB11 (SOT666)		[2] _	300	mW
	PUMB11 (SOT363)		-	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



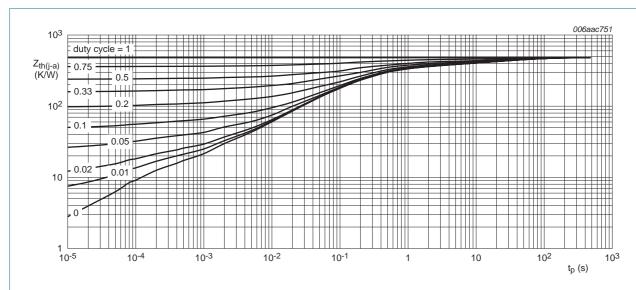
### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PEMB11 (SOT666)		[2] _	-	625	K/W
	PUMB11 (SOT363)		-	-	625	K/W
Per devi	ce					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PEMB11 (SOT666)		[2] _	-	417	K/W
	PUMB11 (SOT363)		-	-	417	K/W

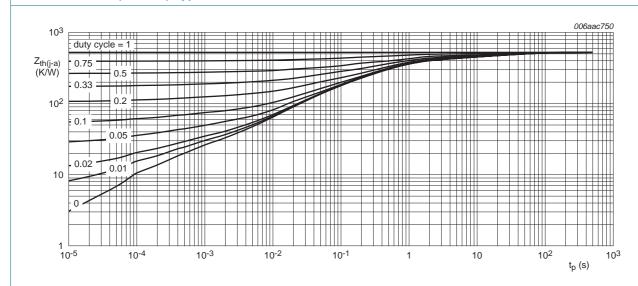
<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PEMB11 (SOT666); typical values



FR4 PCB, standard footprint

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PUMB11 (SOT363); typical values

PNP/PNP resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

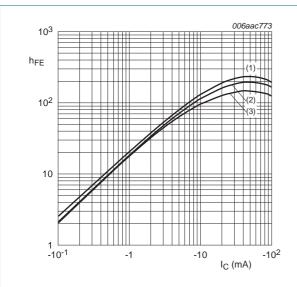
### 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Doromotor	Conditions	Min	Tyrn	Max	Lloit
Symbol	Parameter	Conditions	IVIIN	Тур	Max	Unit
Per trans	istor					
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
OLO	collector-emitter	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	-1	μΑ
	cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$	-	-	<b>-5</b>	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-400	μА
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	-30	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-1.1	-0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -10 \text{ mA}$	-2.5	-1.8	-	V
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		0.8	1.0	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CB} = -5 \text{ V}; I_{C} = -10 \text{ mA};$ f = 100 MHz	<u>[1]</u> -	180	-	MHz

<sup>[1]</sup> Characteristics of built-in transistor.



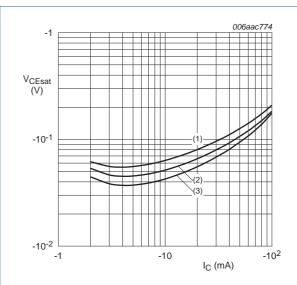
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 4. DC current gain as a function of collector current; typical values



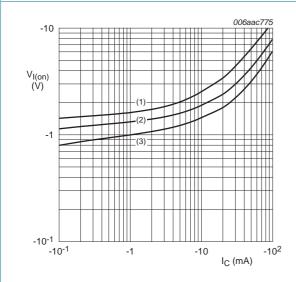
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



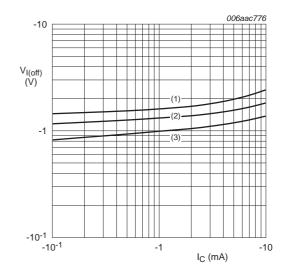
$$V_{CE} = -0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 6. On-state input voltage as a function of collector current; typical values



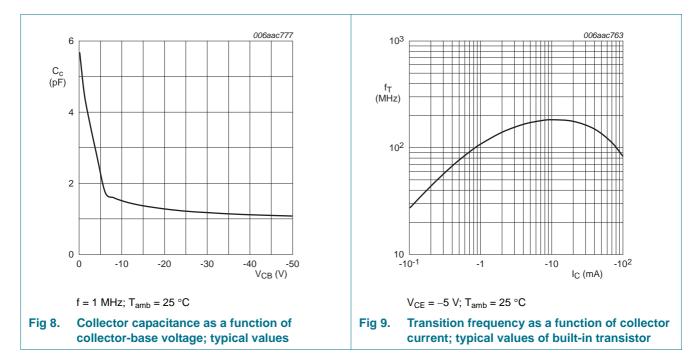
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Off-state input voltage as a function of collector current; typical values

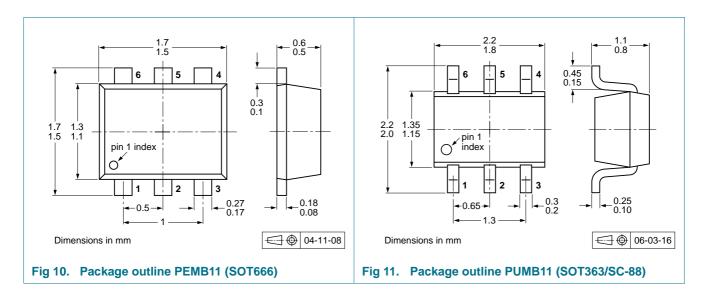


### 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



PEMB11\_PUMB11

### 10. Packing information

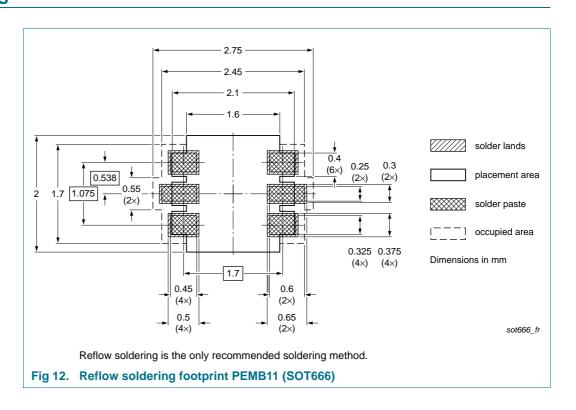
Table 9. Packing methods

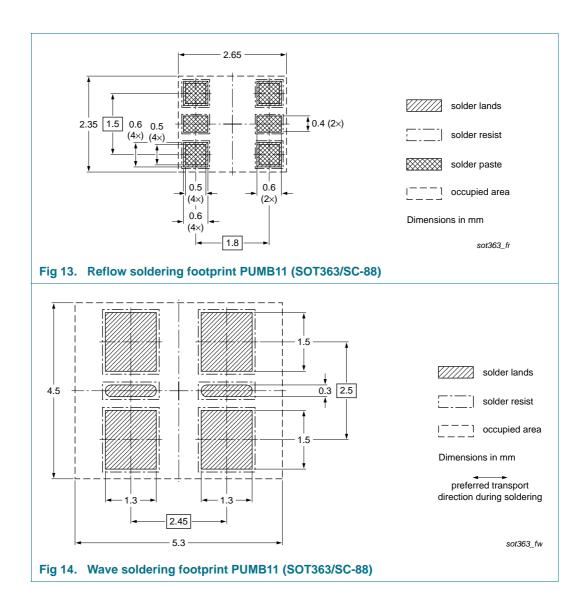
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

		<u> </u>					
Type number	Package	Description		Packii	ng quar	ntity	
				3000	4000	8000	10000
PEMB11	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PUMB11	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

### 11. Soldering





PNP/PNP resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

### 12. Revision history

#### Table 10. Revision history

,							
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PEMB11_PUMB11 v.3	20111130	Product data sheet	-	PEMB11_PUMB11 v.2			
Modifications:		of this document has been f NXP Semiconductors.	redesigned to com	ply with the new identity			
	<ul> <li>Legal texts h</li> </ul>	nave been adapted to the r	new company nam	e where appropriate.			
	<ul> <li>Section 1 "P</li> </ul>	roduct profile": updated					
	<ul> <li>Section 4 "N</li> </ul>	larking": updated					
	• Table 7 "The	ermal characteristics": upda	ated according to the	ne latest measurements			
	<ul> <li><u>Table 8 "Characteristics"</u>: I<sub>CEO</sub> updated according to the latest measurements, V<sub>i(on)</sub></li> <li>V<sub>i(off)</sub> changed respectively to V<sub>I(on)</sub> and V<sub>I(off)</sub>, f<sub>T</sub> added</li> </ul>						
	• Figure 1 to 9	added:					
	<ul> <li>Section 8 "Telling"</li> </ul>	est information": added					
	<ul> <li>Figure 11 and 10: replaced by minimized package outline drawings</li> </ul>						
	<ul><li>Section 10 "</li></ul>	Packing information": adde	ed				
	<ul> <li>Section 11 "</li> </ul>	Soldering": added					
	<ul><li>Section 13 "</li></ul>	Legal information": update	d				
PEMB11_PUMB11 v.2	20031003	Product data sheet	-	PEMB11 v.1 PUMB11 v.1			
PEMB11 v.1	20010913	Preliminary specification	-	-			
PUMB11 v.1	20000808	Product specification	-	-			

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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PEMB11\_PUMB11

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PEMB11; PUMB11

PNP/PNP resistor-equipped transistors; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$ 

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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